

Re-entrant Layer-by-Layer Etching of GaAs(001)

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Abstract

We report the first observation of re-entrant layer-by-layer etching based on *in situ* reflection high-energy electron-diffraction measurements. With AsBr₃ used to etch GaAs(001), sustained specular-beam intensity oscillations are seen at high substrate temperatures, a decaying intensity with no oscillations at intermediate temperatures, but oscillations reappearing at still lower temperatures. Simulations of an atomistic model for the etching kinetics reproduce the temperature ranges of these three regimes and support an interpretation of the origin of this phenomenon as the site-selectivity of the etching process combined with activation barriers to interlayer adatom migration.

81.60.Cp, 05.70.Ln, 68.35.Fx

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The development of *in situ* processing methodologies, where sample preparation, growth, and post-growth modification are all carried out in ultra-high vacuum, is crucial for the reproducible fabrication of atomic-scale heterostructures. To date, most fundamental studies of direct relevance to heterostructure formation have focused on the growth process. However, the removal of atoms during processes such as sputtering and etching also provides a way of manipulating surface properties and morphology. Several recent studies have used electron and helium-atom diffraction and scanning tunnelling microscopy to investigate the atomistic kinetics during the removal of atoms from a surface by low-energy ion-beam sputtering [1–4]. These studies, as well as computer simulations [5–7], have revealed a close correspondence with the processes that occur during epitaxial growth, with monovacancies and vacancy islands playing the roles of adatoms and adatom islands, respectively. It has also been clearly demonstrated by Tsang *et al.* [8,9], using reflection high-energy electron-diffraction (RHEED), that the chemical etching of III-V semiconductor surfaces by molecular beams of PCl_3 and AsCl_3 can occur on a layer-by-layer basis.

The focus of this Letter is on a process related to that studied by Tsang *et al.*, the chemical etching of $\text{GaAs}(001)$ by AsBr_3 . By using *in situ* RHEED measurements, we observe sustained specular intensity oscillations at high substrate temperatures, a decaying intensity with no oscillations at intermediate temperatures, but oscillations reappearing at still lower temperatures. To our knowledge, this is the first report of such re-entrant behavior during a removal process, although re-entrant layer-by-layer *growth* was reported by Kunkel *et al.* [10] for homoepitaxy on $\text{Pt}(111)$. Based on our simulations of the etching kinetics, we propose that the layer-by-layer removal in the lowest temperature range is due to a decrease in the vacancy island sizes combined with the site-selective nature of this etching process.

The experiments were carried out in a conventional molecular-beam epitaxy (MBE) chamber on nominally singular ($0 \pm 0.05^\circ$) $\text{GaAs}(001)$ substrates. After mounting in the system, the substrates were pre-cleaned in an As_2 flux at $\approx 580^\circ\text{C}$ to produce a well-defined 2×4 reconstructed surface. A buffer layer of thickness $\approx 1000 \text{ \AA}$ was grown on this surface also at $\approx 580^\circ\text{C}$ from Ga and As_2 beams to produce a smooth starting surface, as indicated

by comparatively short, narrow RHEED streaks. AsBr_3 was then introduced directly into the MBE chamber without a carrier gas. A concomitant As_2 flux was supplied to avoid any possibility of thermal dissociation of the substrate. The background pressure during etching was 10^{-8} torr. Details of the experiments will be published elsewhere [11].

RHEED measurements were carried out with an electron beam energy of 12.0 keV at an incident angle of $\approx 1^\circ$ along the $[010]$ azimuth. Using these diffraction conditions, maxima in the specular beam intensity correspond to (As-Ga) bilayer increments in the removal of material for a 2×4 reconstructed surface [12]. A slight complication is the fact that the same surface reconstruction could not be maintained over the entire temperature range. At high temperatures, the diffraction pattern showed that the 2×4 reconstruction was prevalent, while at lower temperatures there appeared to be a mixture of 2×4 and $c(4\times 4)$ reconstructions. By analogy with growth, where a change in reconstruction (usually from 2×4 to 3×1 or the reverse) can produce a change in the “phase” or amplitude of the oscillations [13], but never eliminate them, we believe that reconstruction changes cannot be responsible for the re-entrant oscillations observed here. Only the suppression of the layer-by-layer growth (etching) mode in which layers are formed periodically by the nucleation, growth, and coalescence of adatom (vacancy) islands can eliminate the oscillatory behavior.

The RHEED specular beam intensities are shown in Fig. 1 for a range of substrate temperatures. The re-entrant behavior of the oscillations is clearly evident. Although not shown, the temperature range over which the oscillations disappear is very narrow, extending only over $\approx 10^\circ\text{C}$. The RHEED pattern in this range shows well-defined spots soon after etching commences, which is indicative of transmission through three-dimensional asperities on the surface. Above and below this temperature range, the RHEED pattern is streaked over the duration of the measurement.

The inset to Fig. 1 shows the substrate temperature-dependence of the etching rate as deduced from the period of the RHEED intensity oscillations, calibrated absolutely at 580°C by a Talystep measurement on a masked substrate. This rate is nearly constant above 420°C but diminishes rapidly below this temperature [14]. We conclude that above 420°C

the removal is *supply-rate limited* and below 420°C it is *reaction-rate limited*. In particular, the re-entrant behavior is not due to any pathology in the AsBr_3 decomposition rate over the temperature range of interest, but can be traced to factors involving surface morphology and the kinetics of the atomistic processes. The important chemical factor is that the etchant removes Ga atoms as volatile GaBr_x ($x=1, 2$ or 3), but our measurements provide no direct information on reaction pathways.

To model the observations summarized in Fig. 1, we modify a kinetic Monte Carlo model developed for ion-beam sputtering [6,7]. We include a site selectivity whereby atoms with low coordination are preferentially removed from the surface, as described below. Such site selectivity was investigated previously but found to be at most of minor importance for ion-beam sputtering of semiconductor surfaces [5]. In contrast to the simulations in Ref. [5], our model leads to an etching rate that is *independent* of the surface morphology, as required by the constant etching rate above 420°C shown in Fig. 1.

In our simulations, the substrate has a simple cubic structure [15] with neither bulk vacancies nor overhangs allowed (the solid-on-solid model). Atoms are removed from the substrate at the experimentally observed rate of etching by first selecting a site randomly, then searching within a square of a fixed linear size L , centered at the originally selected site, for the surface atom with the fewest lateral nearest neighbors. This atom is then removed from the surface. Surface migration is modeled as a nearest-neighbor hopping process with the rate $k(E, T) = k_0 \exp(-E/k_B T)$, where E is the hopping barrier, T is the substrate temperature, and k_B is Boltzmann's constant. The pre-factor k_0 is taken to be the vibrational frequency of a surface adatom and assigned the value $2k_B T/h$ where h is Planck's constant. The hopping barrier is the sum of a substrate term, E_S , a lateral nearest-neighbor contribution, E_{NN} , and a step-edge barrier. The nearest-neighbor contribution is $E_{NN} = \frac{1}{2}n_1 E_N + E'_N$, where E'_N is nonzero only if the number of lateral nearest neighbors before a hop, n_1 , is greater than that after the hop, n_2 , in which case $E'_N = \frac{1}{2}(n_1 - n_2)E_N$. This definition increases diffusion along island edges and leads to high vacancy mobility (consistent with experimental observations [1–4]) but preserves the difference in the hopping

rate of edge atoms with different coordination as well as the activation barriers to detachment of atoms from step edges ($E_{NN} = n_1 E_N$ for $n_2 = 0$). The vicinity of a step is detected by counting the number of next-nearest neighbors in layers above and below the hopping atom before (m_1) and after (m_2) a hop. An additional (step-edge) barrier to hopping is present only if $m_1 > m_2$, in which case it equals $(m_1 - m_2)E_B$, where E_B is a model parameter.

The simulations were carried out on 200×200 lattices with periodic boundary conditions and $E_S = 1.58$ eV, $E_N = 0.24$ eV, $E_B = 0.175$ eV. When used for simulations of the *growth* of GaAs(001), these parameters produced excellent quantitative agreement with RHEED measurements for a range of growth conditions [12,16]. The parameter L was set equal to 3. Comparisons with the RHEED measurements are based on the continuous monitoring of the surface step density, which is an approximate analog of the RHEED specular-beam intensity under the diffraction conditions used [12,16]. We also calculate the kinematic intensity at anti-Bragg diffraction conditions, which is relevant for other diffraction techniques (e.g., He-atom scattering, grazing-incidence X-ray diffraction). All results presented are averaged over at least five independent simulations.

The results of the simulation are shown in Fig. 2. The re-entrant nature of the RHEED oscillations is seen to be reproduced by the behavior of the step density in the simulations. Kinematic intensity oscillations do not disappear in the intermediate temperature, but are much better defined for both lower and higher temperatures. Notice that the ranges of temperatures at which the oscillations are observed correspond well to those in Fig. 1. The temperature range over which the oscillations disappear (not shown) is very narrow, in qualitative agreement with the experiment.

Based on the experimental measurements and our simulations, the explanation of the re-entrant etching oscillations we propose is as follows. Etching creates surface vacancies which diffuse on the surface and form islands. As these islands grow, new vacancies are created in lower layers within the flat regions near their centers. At high temperatures ($\gg 460^\circ\text{C}$), there are many free adatoms on the surface. Due to the high thermal mobility of adatoms and vacancies, the vacancies created in lower layers are filled in [17]. This results in the

periodic removal of individual layers through the formation, accretion, and coalescence of vacancy islands. The interlayer atomic transport in this temperature range is appreciable because the high density of free adatoms dominates the inhibiting effect of the step-edge barrier.

At intermediate temperatures ($\approx 460^\circ\text{C}$) the number of free adatoms on the surface is reduced drastically because the rate of their detachment from step edges decreases exponentially with decreasing temperature. The filling in of vacancies created in lower layers is now strongly hindered by the step-edge barrier and, therefore, vacancy islands in lower layers are formed. These islands are nested inside vacancy islands on higher layers, creating pits (inverse pyramids) in the surface (cf. the scanning-tunneling microscopy images in Refs. [2] and [3]). As a result of this *multilayer*, or *three-dimensional*, mode of removal, a rough surface morphology quickly develops which is qualitatively different from both the low- and high-temperature morphologies (see Refs. [18] and [19] for the growth analog) and is accompanied by the disappearance of RHEED oscillations and the appearance of a spotty diffraction pattern.

Finally, at low temperatures ($\ll 460^\circ\text{C}$), the mobility of vacancies is low, which leads to the formation of many small islands [20] and a high density of atoms with low coordination in the uppermost layer. These atoms are preferentially removed by the etching process which leads to the re-emergence of an approximately layer-by-layer removal mode and the reappearance of RHEED oscillations. The transition from the layer-by-layer removal regime at high temperatures to the multilayer removal regime has been observed in the ion-beam sputtering of Pt(111) [1–3], but obtaining the reappearance of the oscillations at lower temperatures requires a site-selective step such as the one we have proposed [21].

There is an important consequence of our interpretation of the reappearance of RHEED oscillations at low temperatures. If the etching rate is increased in the intermediate temperature regime by supplying more etchant molecules to the substrate, the oscillations should reappear, as if the substrate temperature had been decreased with the original flux maintained. In both cases the vacancy islands become smaller [20], the density of low-coordinated

atoms at the uppermost layer is higher and the site-selective step becomes more important. Fig. 3 demonstrates that this is indeed the case: as the etching rate is increased, oscillations reappear at 460°C (cf. Fig. 1) and their amplitude grows with the etching rate. An analogous effect is observed in the simulations. Note that the oscillations reappear even for a modest change of the etching rate (a factor of 2) due to the vacancy islands at the chosen temperature being just large enough to make the preferential etching of atoms with low coordination unimportant. Thus, even a small decrease in the island sizes brings the oscillations back. The result shown in Fig. 3 demonstrates once more that the re-entrance of oscillations involves the surface morphology and not the change in the etching reaction rate with the temperature.

In conclusion, we have reported the first observation of the re-entrant layer-by-layer etching of a solid surface. Based on simulations of the etching kinetics, we propose that the RHEED oscillations indicating layer-by-layer etching disappear in the intermediate temperature regime because of the increasing importance of the barriers to interlayer hopping and the decreasing number of free adatoms on the surface. The reappearance of the oscillations at still lower temperatures is due to a decrease of the vacancy island sizes combined with the site-selective nature of the etching process whereby atoms with low coordination are preferentially removed from the surface.

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FIGURES

FIG. 1. RHEED specular-beam intensity evolution during etching of GaAs(001) with an AsBr₃ flux of 0.36 sccm and different substrate temperatures. The inset shows the etching rate vs. the substrate temperature.

FIG. 2. The surface step density and the specular-beam intensity calculated in the kinematic approximation for an anti-Bragg angle of incidence during growth at three different substrate temperatures. The step density increases *downwards*. The upper two curves in both plots are given offsets to make comparisons easier.

FIG. 3. RHEED specular-beam intensity evolution during etching of GaAs(001) at a substrate temperature of 460°C but with different AsBr₃ fluxes.